

FABRICATING STRAINED CHANNEL  
EPITAXIAL SOURCE/DRAIN TRANSISTORS

Abstract of the Disclosure

The mobility of carriers may be increased in strained channel epitaxial source/drain transistors. Doped silicon material may be blanket deposited after removing ion  
5 implanted source/drain regions. The blanket deposition forms amorphous films over non-source/drain areas and crystalline films in source/drain regions. By using an etch which is selective to amorphous silicon, the amorphous material may be removed. This may avoid some problems  
10 associated with selective deposition of the doped silicon material.